

SYNTHESIS OF DISTRIBUTED NETWORKS WITH APPLICATIONS TO THE DESIGN
OF ULTRA-WIDEBAND GaAs MESFET POWER AMPLIFIERS

Walter H. Ku
School of Electrical Engineering
Cornell University
Ithaca, New York 14853

Harry A. Willing
Microwave Technology Branch
Naval Research Laboratory
Washington, DC 20375

ABSTRACT

This paper presents design techniques for the CAD and experimental fabrication of ultra-wideband GaAs MESFET power amplifiers which are directed to ECM and EW system applications. Fundamental gain-bandwidth limitations are derived for state-of-the-art GaAs MESFET power devices. Broadband designs are developed in the 2- to 18-GHz range using analytical and computer-aided optimization techniques. These designs are based upon small- and large-signal device characterization and modeling. Presented are systematic procedures required to arrive at the final designs. Modeling techniques and their utilization as a tool in achieving optimum performance are described. Included in this paper is a discussion of the laboratory methods employed to perform small- and large-signal device characterization and analysis. Experimental results on medium-power MIC amplifiers covering the entire 6-18 GHz frequency band using submicron gate-length MESFET chips are also presented in the paper.

Full text of paper not available at time of publication.